

HM514256A/AL Series

262,144-Word x 4-Bit CMOS Dynamic RAM

DESCRIPTION

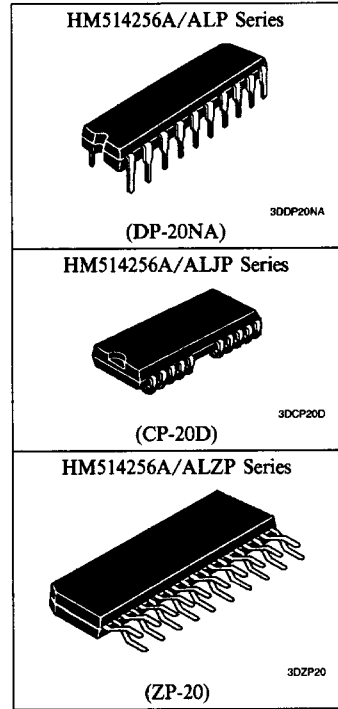
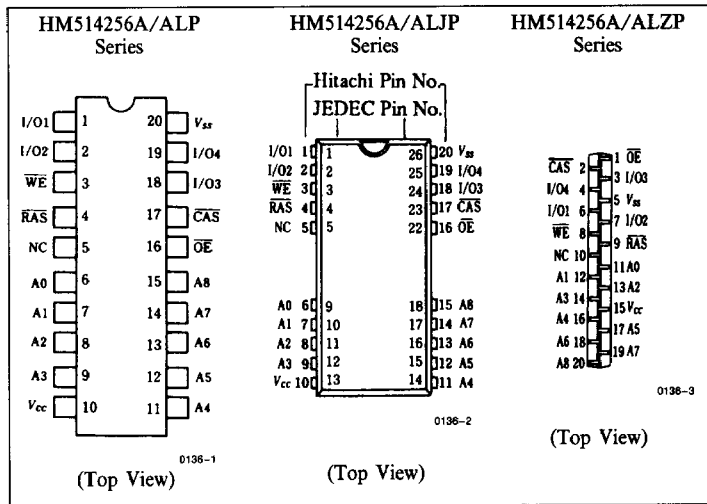
The Hitachi HM514256A/AL is a CMOS dynamic RAM organized 262,144-word x 4-bit. HM514256A/AL has realized higher density, higher performance and various functions by employing 1.3 μ m CMOS technology and some new CMOS circuit design technologies. The HM514256A/AL offers Fast Page Mode as a high speed access mode.

Multiplexed address input permits the HM514256A/AL to be packaged in standard 20-pin plastic DIP, 20-pin plastic SOJ and 20-pin plastic ZIP.

FEATURES

- Single 5V ($\pm 10\%$)
- High Speed
 - Access Time 60 ns/70 ns/80 ns/100 ns/120 ns (max)
- Low Power
 - Standby 11 mW (max), 1.7 mW (max) (L Version)
 - Active 495 mW/440 mW/363 mW/302.5 mW/258.5 mW (max)
- Fast Page Mode Capability
- 512 Refresh Cycles (8 ms), (64 ms) (L Version)
- 2 Variations of Refresh
 - $\overline{\text{RAS}}$ Only Refresh
 - CAS Before $\overline{\text{RAS}}$ Refresh

PIN OUT



PIN DESCRIPTION

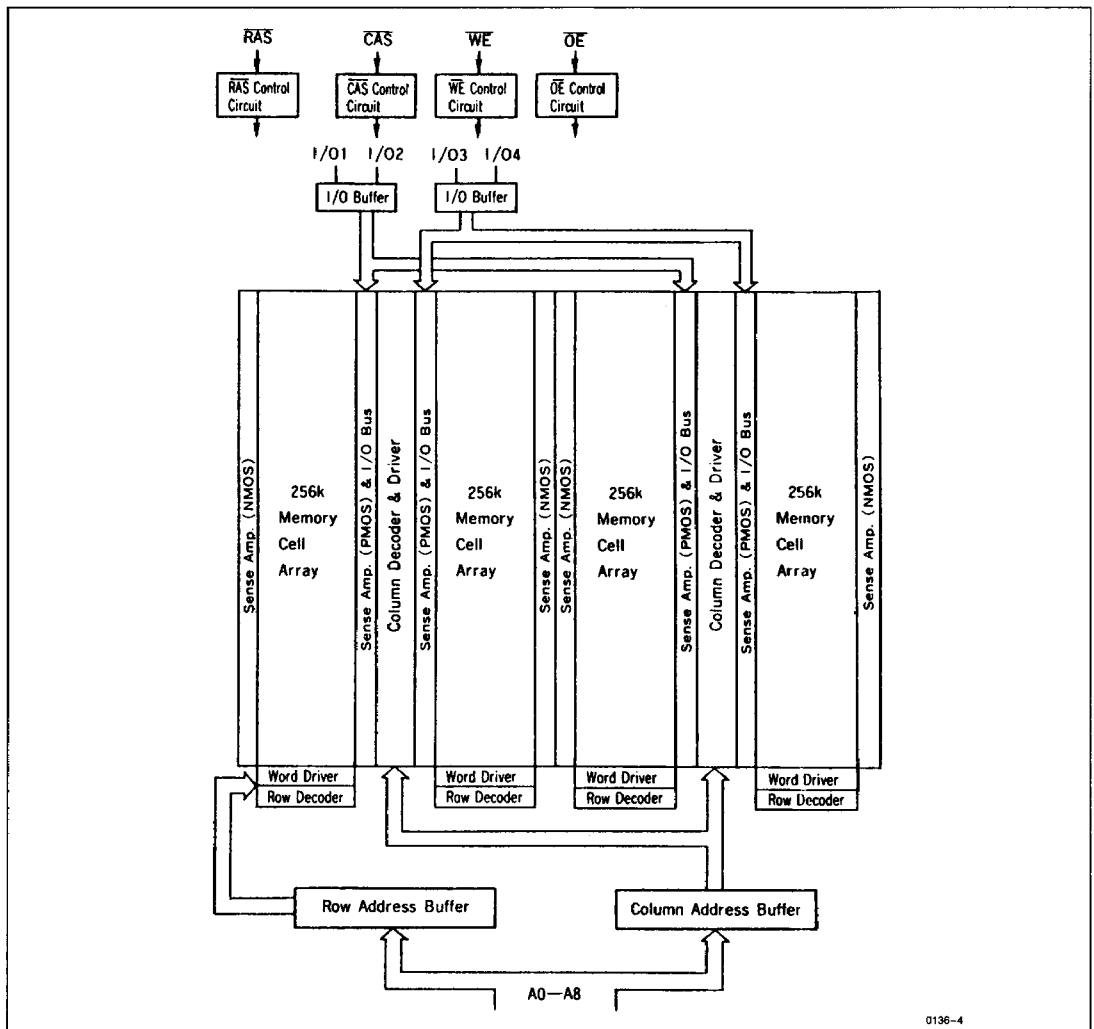
Pin Name	Function
A ₀ -A ₈	Address Input
A ₀ -A ₈	Refresh Address Input
I/O ₁ -I/O ₄	Data Input/Data Output
$\overline{\text{RAS}}$	Row Address Strobe
$\overline{\text{CAS}}$	Column Address Strobe
$\overline{\text{WE}}$	Write Enable
$\overline{\text{OE}}$	Output Enable
V _{CC}	Power Supply (+ 5V)
V _{SS}	Ground



■ ORDERING INFORMATION

Part No.	Access Time	Package	Part No.	Access Time	Package
HM514256AP-6	60 ns	300-mil 20-pin Plastic DIP (DP-20NA)	HM514256ALP-6	60 ns	300-mil 20-pin Plastic DIP (DP-20NA)
HM514256AP-7	70 ns		HM514256ALP-7	70 ns	
HM514256AP-8	80 ns		HM514256ALP-8	80 ns	
HM514256AP-10	100 ns		HM514256ALP-10	100 ns	
HM514256AP-12	120 ns		HM514256ALP-12	120 ns	
HM514256AJP-6	60 ns	300-mil 20-pin Plastic SOJ (CP-20D)	HM514256ALJP-6	60 ns	300-mil 20-pin Plastic SOJ (CP-20D)
HM514256AJP-7	70 ns		HM514256ALJP-7	70 ns	
HM514256AJP-8	80 ns		HM514256ALJP-8	80 ns	
HM514256AJP-10	100 ns		HM514256ALJP-10	100 ns	
HM514256AJP-12	120 ns		HM514256ALJP-12	120 ns	
HM514256AZP-6	60 ns	400-mil 20-pin Plastic ZIP (ZP-20)	HM514256ALZP-6	60 ns	400-mil 20-pin Plastic ZIP (ZP-20)
HM514256AZP-7	70 ns		HM514256ALZP-7	70 ns	
HM514256AZP-8	80 ns		HM514256ALZP-8	80 ns	
HM514256AZP-10	100 ns		HM514256ALZP-10	100 ns	
HM514256AZP-12	120 ns		HM514256ALZP-12	120 ns	

■ BLOCK DIAGRAM



■ ABSOLUTE MAXIMUM RATINGS

Item	Symbol	Value	Unit
Voltage on Any Pin Relative to V_{SS}	V_T	- 1.0 to + 7.0	V
Supply Voltage Relative to V_{SS}	V_{CC}	- 1.0 to + 7.0	V
Short Circuit Output Current	I_{out}	50	mA
Power Dissipation	P_T	1.0	W
Operating Temperature	T_{opr}	0 to + 70	°C
Storage Temperature	T_{stg}	- 55° to + 125	°C

■ ELECTRICAL CHARACTERISTICS

• Recommended DC Operating Conditions ($T_A = 0$ to +70°C)

Item	Symbol	Min	Typ	Max	Unit	Note
Supply Voltage	V_{SS}	0	0	0	V	
	V_{CC}	4.5	5.0	5.5	V	1
Input High Voltage	V_{IH}	2.4	—	6.5	V	1
Input Low Voltage	I/O Pin V_{IL}	- 1.0	—	0.8	V	1
	Others V_{IL}	- 2.0	—	0.8	V	1

Note: 1. All voltage reference to V_{SS} .

• DC Characteristics ($T_A = 0$ to +70°C, $V_{CC} = 5V \pm 10\%$, $V_{SS} = 0V$)

Item	Symbol	HM514256										Unit	Test Conditions	Note
		A/AL-6		A/AL-7		A/AL-8		A/AL-10		A/AL-12				
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max			
Operating Current	I_{CC1}	—	90	—	80	—	66	—	55	—	47	mA	\overline{RAS} , \overline{CAS} Cycling, $t_{RC} = \text{Min}$	1, 2
Standby Current	I_{CC2}	—	2	—	2	—	2	—	2	—	2	mA	\overline{RAS} , $\overline{CAS} = V_{IH}$ $D_{out} = \text{High-Z}$ TTL Interface	
		—	1	—	1	—	1	—	1	—	1	mA	\overline{RAS} , $\overline{CAS} \geq V_{CC} - 0.2V$ CMOS Interface	
		—	300	—	300	—	300	—	300	—	300	μA	$D_{out} = \text{High-Z}$ CMOS Interface L-Version	
\overline{RAS} Only Refresh Current	I_{CC3}	—	90	—	80	—	66	—	55	—	47	mA	$t_{RC} = \text{Min}$	2
Battery Backup Current (Only for L-Version)	I_{CC4}	—	300	—	300	—	300	—	300	—	300	μA	$t_{RC} = 125 \mu s$ \overline{CAS} Before \overline{RAS} Cycling	4
Standby Current	I_{CC5}	—	5	—	5	—	5	—	5	—	5	mA	$\overline{RAS} = V_{IH}$ $\overline{CAS} = V_{IL}$ $D_{out} = \text{Enable}$	1
\overline{CAS} Before \overline{RAS} Refresh Current	I_{CC6}	—	80	—	70	—	66	—	55	—	47	mA	$t_{RC} = \text{Min}$	
Fast Page Mode Current	I_{CC7}	—	80	—	70	—	55	—	55	—	47	mA	$t_{PC} = \text{Min}$	1, 3
Input Leakage Current	I_{LI}	- 10	10	- 10	10	- 10	10	- 10	10	- 10	10	μA	$0V \leq V_{in} \leq 7V$	
Output Leakage Current	I_{LO}	- 10	10	- 10	10	- 10	10	- 10	10	- 10	10	μA	$0V \leq V_{out} \leq 7V$ $D_{out} = \text{Disable}$	



• DC Characteristics (T_A = 0 to +70°C, V_{CC} = 5V ± 10%, V_{SS} = 0V) (continued)

Item	Symbol	HM514256										Unit	Test Conditions	Note
		A/AL-6		A/AL-7		A/AL-8		A/AL-10		A/AL-12				
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max			
Output High Voltage	V _{OH}	2.4	V _{CC}	2.4	V _{CC}	2.4	V _{CC}	2.4	V _{CC}	2.4	V _{CC}	V	High I _{out} = -5 mA	
Output Low Voltage	V _{OL}	0	0.4	0	0.4	0	0.4	0	0.4	0	0.4	V	Low I _{out} = 4.2 mA	

- Notes: 1. I_{CC} depends on output loading condition when the device is selected. I_{CC} (max) is specified at the output open condition.
 2. Address can be changed less than three times while $\overline{RAS} = V_{IL}$.
 3. Address can be changed once or less while $\overline{CAS} = V_{IH}$.
 4. t_{RAS} = t_{RAS} (min) to 1 μs.
 Input Voltage: I/O Pins: V_{IH} ≥ V_{CC} - 0.2V, V_{IL} ≤ 0.2V or High-Z
 The Other Pins: V_{IH} ≥ V_{CC} - 0.2V, or V_{IL} ≤ 0.2V

• Capacitance (T_A = 25°C, V_{CC} ± 10%)

Item	Symbol	Typ	Max	Unit	Note	
Input Capacitance	Address	C _{I1}	—	5	pF	1
	Clock	C _{I2}	—	7	pF	1
Input/Output Capacitance	Data Input/Data Output	C _{I/O}	—	10	pF	1, 2

- Notes: 1. Capacitance measured with Boonton Meter or effective capacitance measuring method.
 2. $\overline{CAS} = V_{IH}$ to disable D_{out}.

• AC Characteristics (T_A = 0 to +70°C, V_{CC} = 5V ± 10%, V_{SS} = 0V)¹⁴

Test Conditions

- Input Rise and Fall Times 5 ns
 Input Timing Reference Levels 0.8V, 2.4V
 Output Load 2 TTL Gate + C_L (100 pF)
 (Including Scope and Jig)

Read, Write, Read-Modify-Write and Refresh Cycles (Common Parameters)

Item	Symbol	HM514256										Unit	Note
		A/AL-6		A/AL-7		A/AL-8		A/AL-10		A/AL-12			
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max		
Random Read or Write Cycle Time	t _{RC}	120	—	130	—	160	—	190	—	220	—	ns	
\overline{RAS} Precharge Time	t _{RP}	50	—	50	—	70	—	80	—	90	—	ns	
\overline{RAS} Pulse Width	t _{RAS}	60	10000	70	10000	80	10000	100	10000	120	10000	ns	
\overline{CAS} Pulse Width	t _{CAS}	20	10000	20	10000	25	10000	25	10000	30	10000	ns	
Row Address Setup Time	t _{ASR}	0	—	0	—	0	—	0	—	0	—	ns	
Row Address Hold Time	t _{RAH}	10	—	10	—	12	—	15	—	15	—	ns	
Column Address Setup Time	t _{ASC}	0	—	0	—	0	—	0	—	0	—	ns	
Column Address Hold Time	t _{CAH}	15	—	15	—	20	—	20	—	25	—	ns	
\overline{RAS} to \overline{CAS} Delay Time	t _{RCD}	20	40	20	50	22	55	25	75	25	90	ns	8
\overline{RAS} to Column Delay Time	t _{RAD}	15	30	15	35	17	40	20	55	20	65	ns	9
\overline{RAS} Hold Time	t _{RSH}	20	—	20	—	25	—	25	—	30	—	ns	
\overline{CAS} Hold Time	t _{CSH}	60	—	70	—	80	—	100	—	120	—	ns	
\overline{CAS} to \overline{RAS} Precharge Time	t _{CRP}	10	—	10	—	10	—	10	—	10	—	ns	



Read, Write, Read-Modify-Write and Refresh Cycles (Common Parameters) (continued)

Item	Symbol	HM514256										Unit	Note
		A/AL-6		A/AL-7		A/AL-8		A/AL-10		A/AL-12			
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max		
OE to D _{in} Delay Time	t _{ODD}	20	—	20	—	20	—	25	—	30	—	ns	
OE Delay Time from D _{in}	t _{DZO}	0	—	0	—	0	—	0	—	0	—	ns	
CAS Delay Time from D _{in}	t _{DZC}	0	—	0	—	0	—	0	—	0	—	ns	
Transition Time (Rise and Fall)	t _T	3	50	3	50	3	50	3	50	3	50	ns	1, 7
Refresh Period	t _{REF}	—	8	—	8	—	8	—	8	—	8	ms	
Refresh Period (Only for L-Version)	t _{REF}	—	64	—	64	—	64	—	64	—	64	ms	

Read Cycle

Item	Symbol	HM514256										Unit	Note
		A/AL-6		A/AL-7		A/AL-8		A/AL-10		A/AL-12			
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max		
Access Time from RAS	t _{RAC}	—	60	—	70	—	80	—	100	—	120	ns	2, 3
Access Time from CAS	t _{CAC}	—	20	—	20	—	25	—	25	—	30	ns	3, 4
Access Time from Address	t _{AA}	—	30	—	35	—	40	—	45	—	55	ns	3, 5
Access Time from OE	t _{OAC}	—	20	—	20	—	25	—	25	—	30	ns	
Read Command Setup Time	t _{RCS}	0	—	0	—	0	—	0	—	0	—	ns	
Read Command Hold Time to CAS	t _{RCH}	0	—	0	—	0	—	0	—	0	—	ns	
Read Command Hold Time to RAS	t _{RRH}	10	—	10	—	10	—	10	—	10	—	ns	
Column Address to RAS Lead Time	t _{RAL}	30	—	35	—	40	—	45	—	55	—	ns	
Output Buffer Turn-off Time	t _{OFF1}	—	20	—	20	—	20	—	25	—	30	ns	6
Output Buffer Turn-off to OE	t _{OFF2}	—	20	—	20	—	20	—	25	—	30	ns	6
CAS to D _{in} Delay Time	t _{CDD}	20	—	20	—	20	—	25	—	30	—	ns	

Write Cycle

Item	Symbol	HM514256										Unit	Note
		A/AL-6		A/AL-7		A/AL-8		A/AL-10		A/AL-12			
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max		
Write Command Setup Time	t _{WCS}	0	—	0	—	0	—	0	—	0	—	ns	10
Write Command Hold Time	t _{WCH}	15	—	15	—	20	—	20	—	25	—	ns	
Write Command Pulse Width	t _{Wp}	10	—	10	—	15	—	15	—	20	—	ns	
Write Command to RAS Lead Time	t _{RWL}	20	—	20	—	25	—	25	—	30	—	ns	
Write Command to CAS Lead Time	t _{CWL}	20	—	20	—	25	—	25	—	30	—	ns	
Data-in Setup Time	t _{DS}	0	—	0	—	0	—	0	—	0	—	ns	11
Data-in Hold time	t _{DH}	15	—	15	—	15	—	20	—	25	—	ns	11



Read-Modify-Write Cycle

Item	Symbol	HM514256										Unit	Note
		A/AL-6		A/AL-7		A/AL-8		A/AL-10		A/AL-12			
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max		
Read-Write Cycle Time	t _{RWC}	170	—	180	—	220	—	255	—	295	—	ns	
RAS to WE Delay Time	t _{RWD}	85	—	95	—	110	—	135	—	160	—	ns	10
CAS to WE Delay Time	t _{CWD}	45	—	45	—	55	—	60	—	70	—	ns	10
Column Address to WE Delay Time	t _{AWD}	55	—	60	—	70	—	80	—	95	—	ns	10
OE Hold Time from WE	t _{OEH}	20	—	20	—	25	—	25	—	30	—	ns	

Refresh Cycle

Item	Symbol	HM514256										Unit	Note
		A/AL-6		A/AL-7		A/AL-8		A/AL-10		A/AL-12			
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max		
CAS Setup Time (CAS Before RAS Refresh Cycle)	t _{CSR}	10	—	10	—	10	—	10	—	10	—	ns	
CAS Hold Time (CAS Before RAS Refresh Cycle)	t _{CHR}	15	—	15	—	20	—	20	—	25	—	ns	
RAS Precharge to CAS Hold Time	t _{RPC}	10	—	10	—	10	—	10	—	10	—	ns	

Fast Page Mode Cycle

Item	Symbol	HM514256										Unit	Note
		A/AL-6		A/AL-7		A/AL-8		A/AL-10		A/AL-12			
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max		
Fast Page Mode Cycle Time	t _{PC}	45	—	50	—	55	—	55	—	65	—	ns	
Fast Page Mode CAS Precharge Time	t _{CP}	10	—	10	—	10	—	10	—	15	—	ns	
Fast Page Mode RAS Pulse Width	t _{RASC}	—	100000	—	100000	—	100000	—	1000000	—	100000	ns	12
Access Time from CAS Precharge	t _{ACP}	—	40	—	45	—	50	—	50	—	60	ns	13
RAS Hold Time from CAS Precharge	t _{RHCP}	40	—	45	—	50	—	50	—	60	—	ns	
Fast Page Mode Read-Write Cycle Time	t _{PCM}	95	—	100	—	110	—	115	—	135	—	ns	

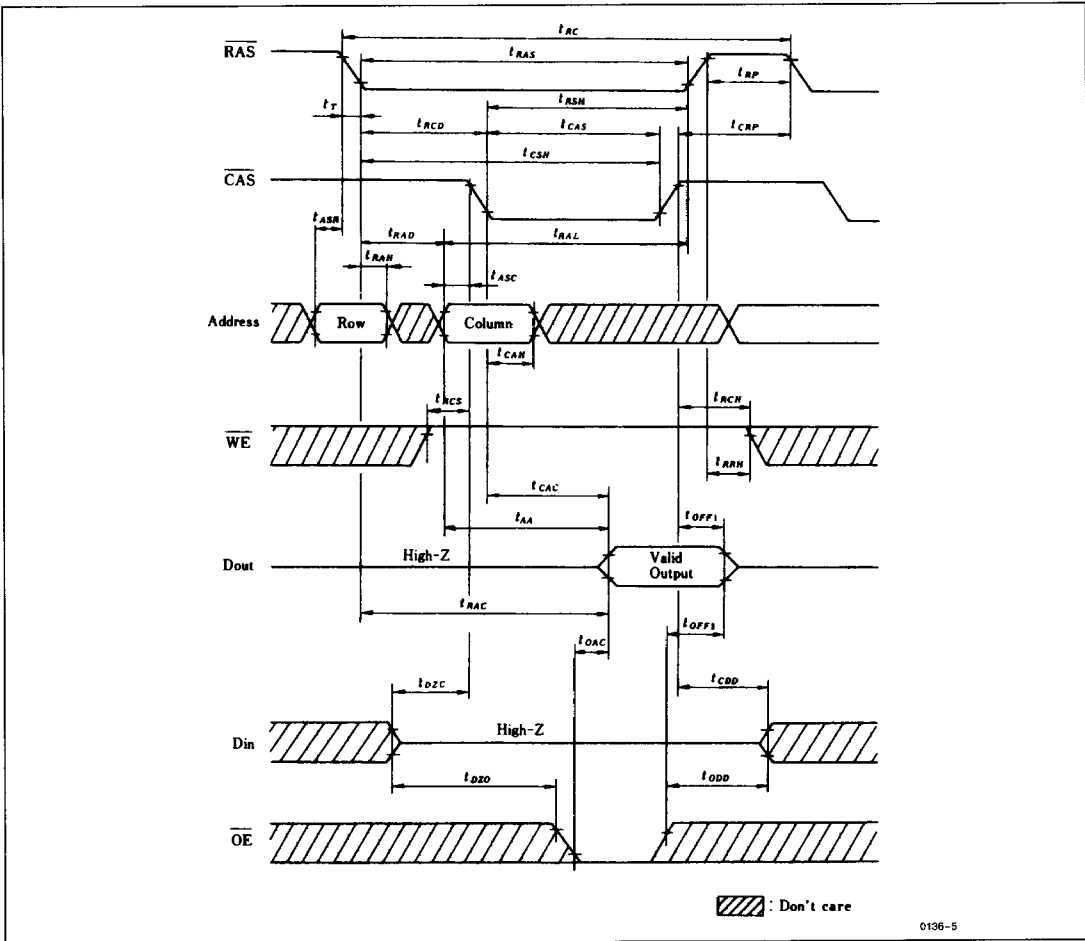
- Notes:
1. AC measurements assume t_T = 5 ns.
 2. Assumes that t_{RCD} ≤ t_{RCD} (max) and t_{RAD} ≤ t_{RAD} (max). If t_{RCD} or t_{RAD} is greater than the maximum recommended value shown in this table, t_{RAC} exceeds the value shown.
 3. Measured with a load circuit equivalent to 2 TTL loads and 100 pF.
 4. Assumes that t_{RCD} ≥ t_{RCD} (max) and t_{RAD} ≤ t_{RAD} (max).
 5. Assumes that t_{RCD} ≤ t_{RCD} (max) and t_{RAD} ≥ t_{RAD} (max).
 6. t_{OFF} (max) is defined as the time at which the output achieves the open circuit condition and is not referenced to output voltage levels.
 7. Transition times are measured between V_{IH} and V_{IL}.
 8. Operation with the t_{RCD} (max) limit insures that t_{RAC} (max) can be met, t_{RCD} (max) is specified as a reference point only, if t_{RCD} is greater than the specified t_{RCD} (max) limit, then access time is controlled exclusively by t_{CAC}.
 9. Operation with the t_{RAD} (max) limit insures that t_{RAC} (max) can be met, t_{RAD} (max) is specified as a reference point only, if t_{RAD} is greater than the specified t_{RAD} (max) limit, then access time is controlled exclusively by t_{AA}.



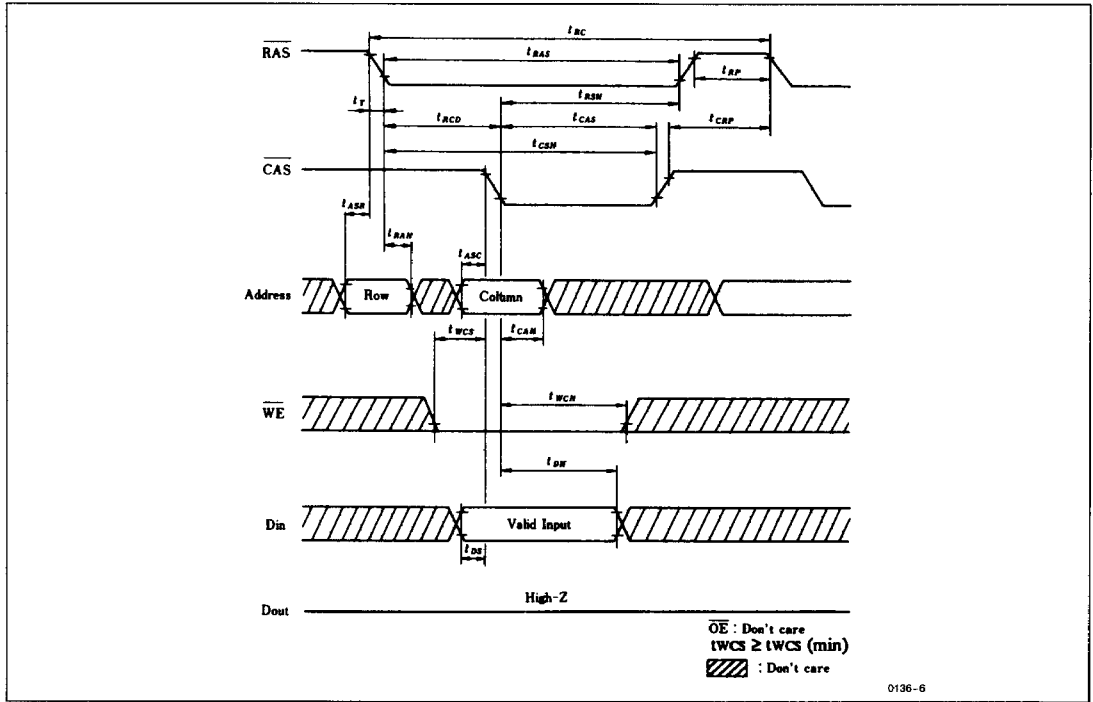
10. t_{WCS} , t_{RWD} , t_{CWD} and t_{AWD} are not restrictive operating parameters. They are included in the data sheet as electrical characteristics only: if $t_{WCS} \geq t_{WCS}(\text{min})$, the cycle is an early write cycle and the data out pin will remain open circuit (high impedance) throughout the entire cycle; if $t_{RWD} \geq t_{RWD}(\text{min})$, $t_{CWD} \geq t_{CWD}(\text{min})$ and $t_{AWD} \geq t_{AWD}(\text{min})$, the cycle is a read-write and the data output will contain data read from the selected cell; if neither of the above sets of conditions is satisfied, the condition of the data out (at access time) is indeterminate.
11. These parameters are referenced to $\overline{\text{CAS}}$ leading edge in early write cycles and to $\overline{\text{WE}}$ leading edge in delayed write or read-modify-write cycles.
12. t_{RASC} is determined by $\overline{\text{RAS}}$ pulse width in fast page mode cycles.
13. Access time is determined by the longer of t_{AA} , t_{CAC} or t_{ACP} .
14. An initial pause of 100 μs is required after power-up followed by eight or more initialization cycles (any combination of cycles containing $\overline{\text{RAS}}$ clock such as $\overline{\text{RAS}}$ only refresh). If the internal refresh counter is used, eight or more $\overline{\text{CAS}}$ before $\overline{\text{RAS}}$ refresh cycles are required.

■ TIMING WAVEFORMS

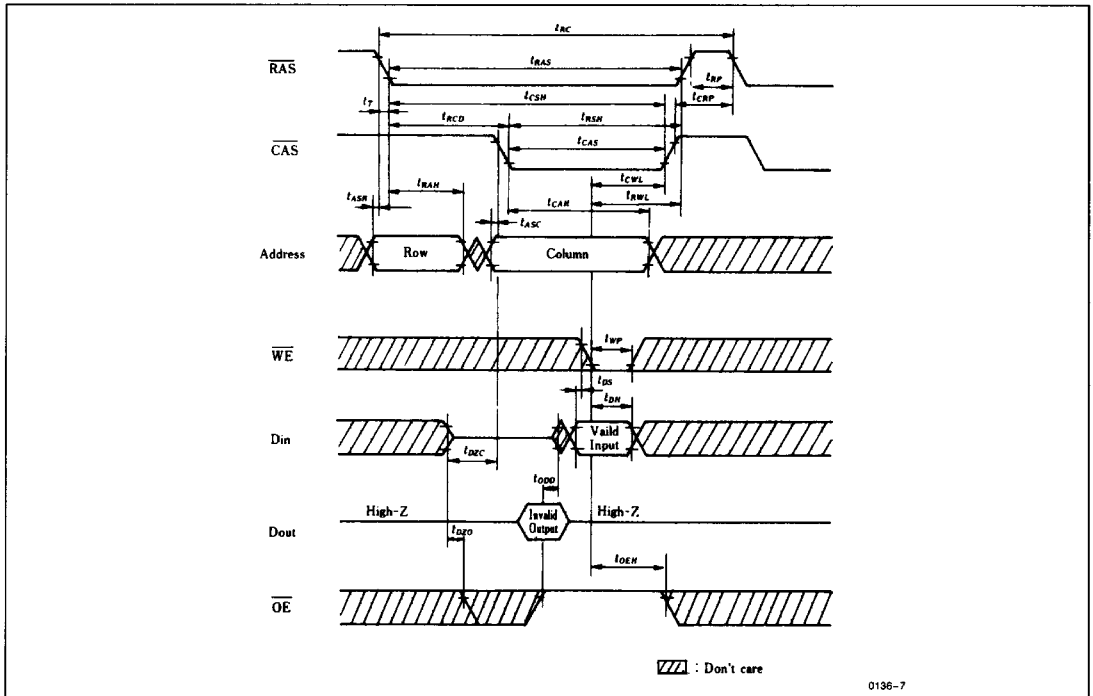
• Read Cycle



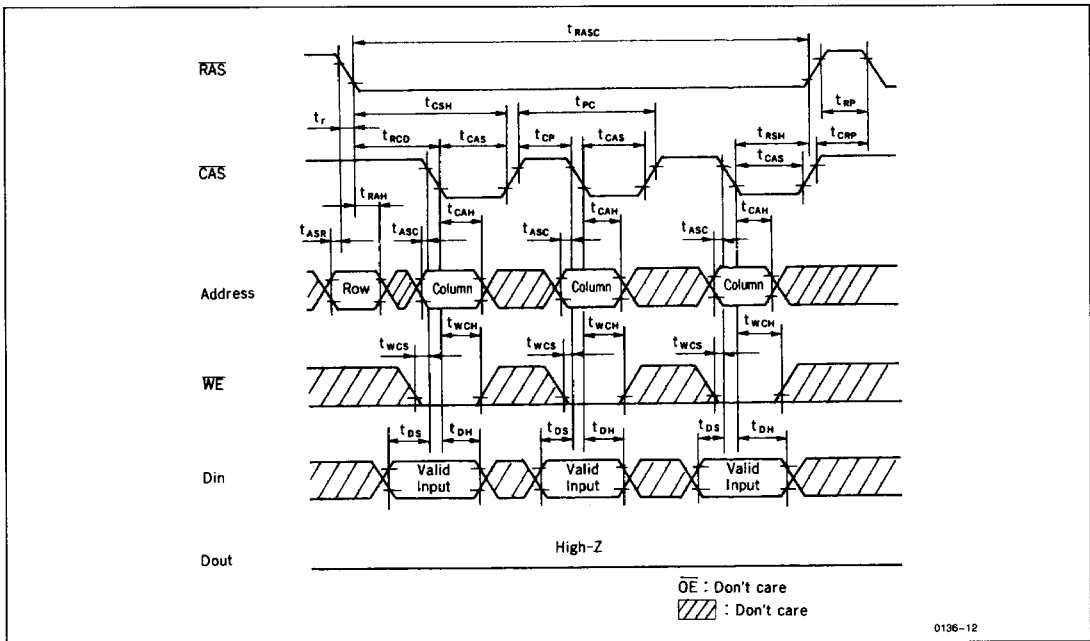
• Early Write Cycle



• Delayed Write Cycle

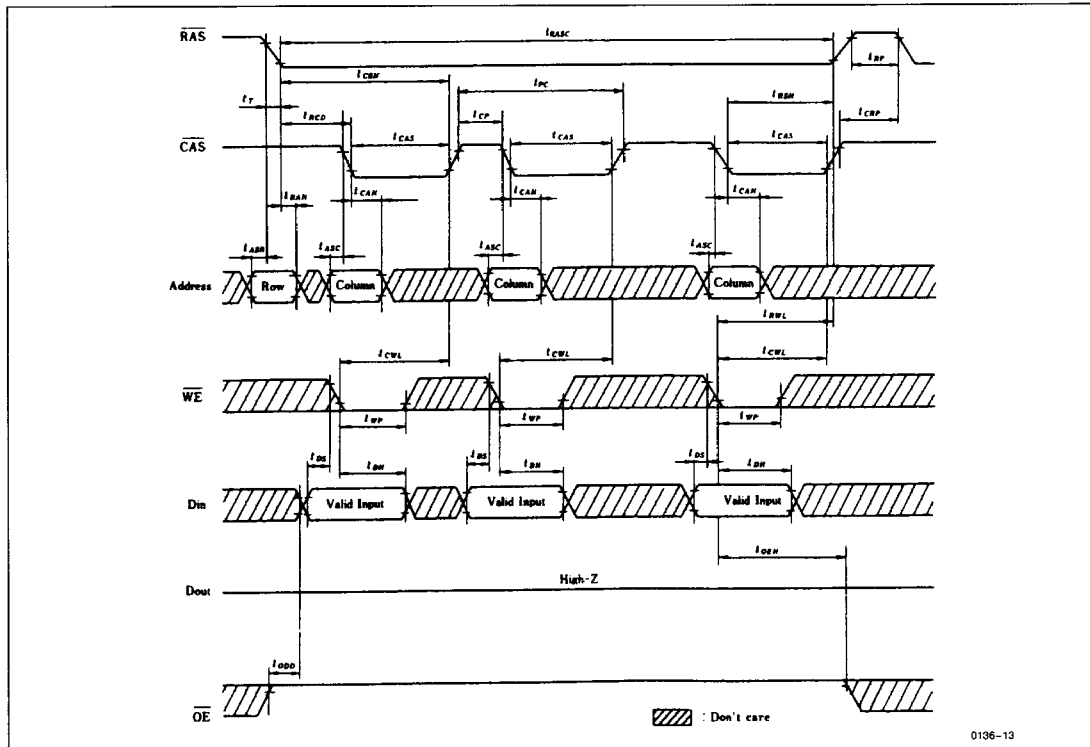


• Fast Page Mode Early Write Cycle



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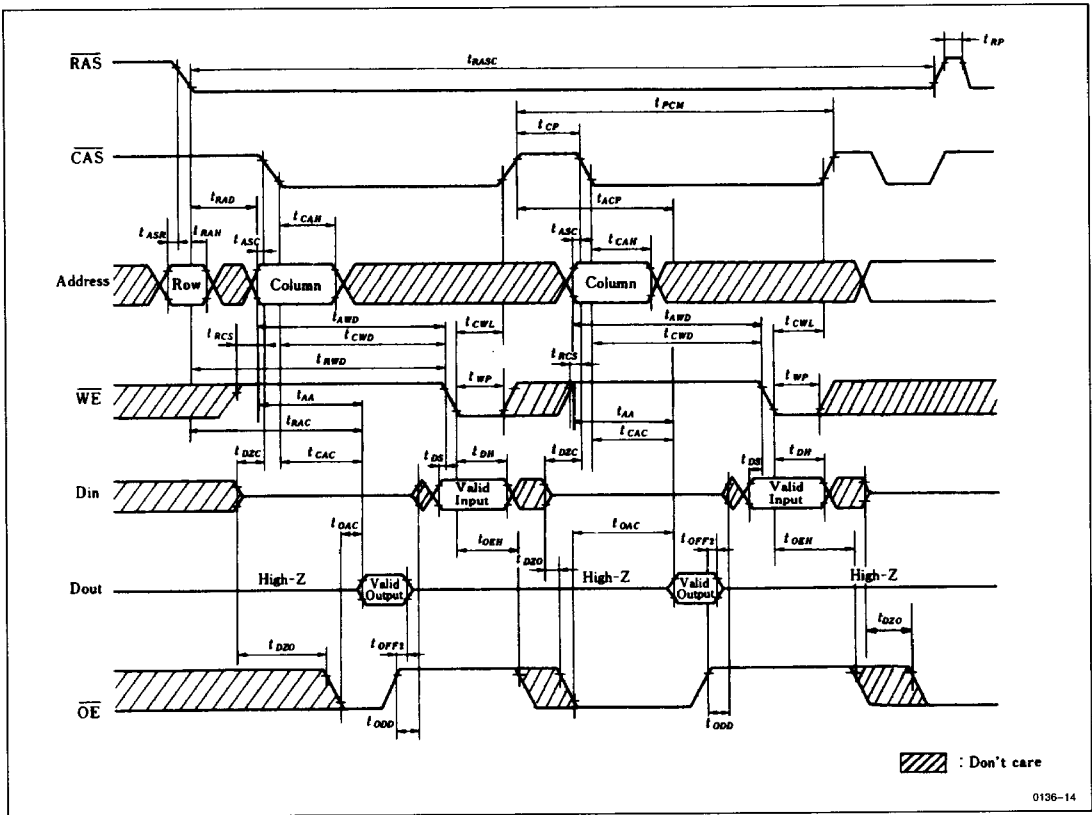
• Fast Page Delayed Write Cycle

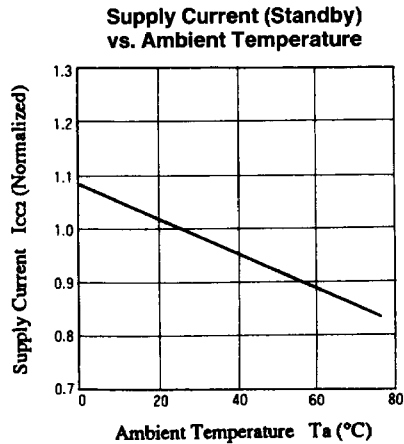
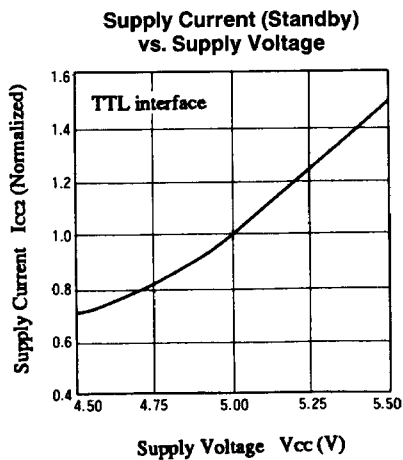
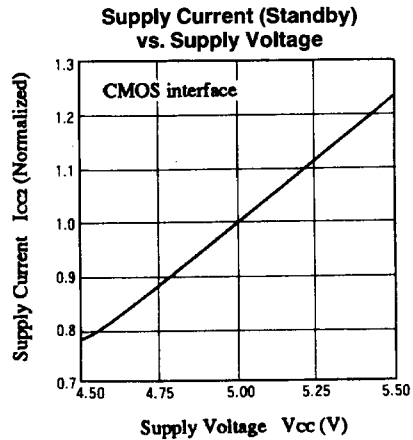
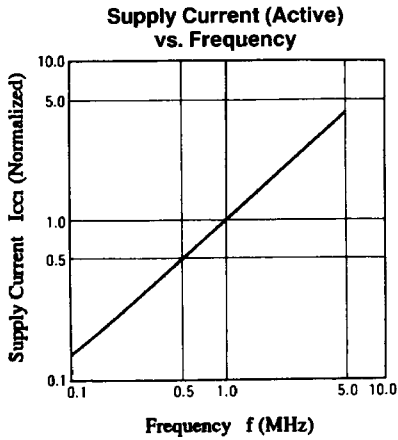
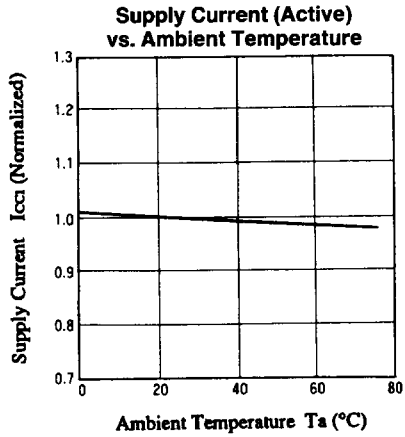
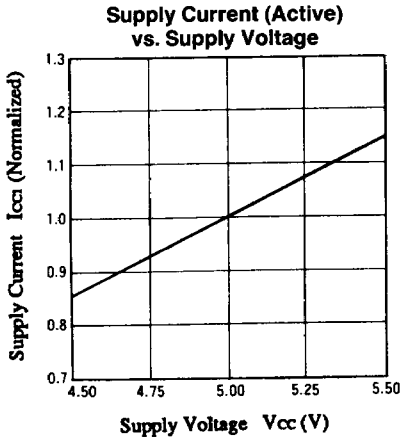


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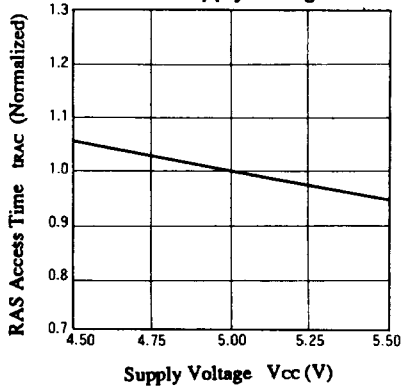


• Fast Page Mode Read-Modify-Write Cycle

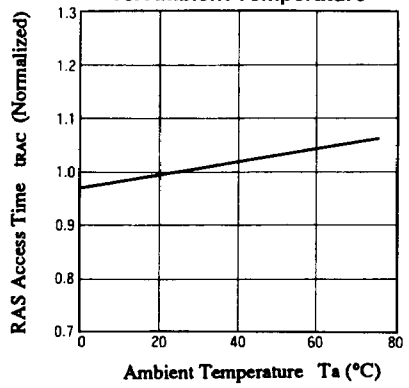




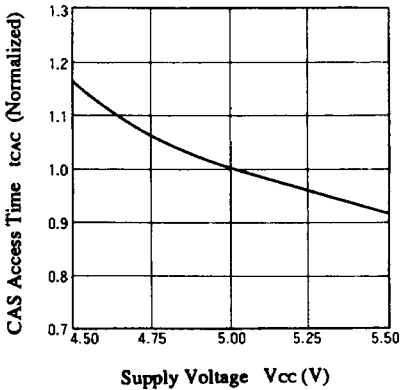
RAS Access Time vs. Supply Voltage



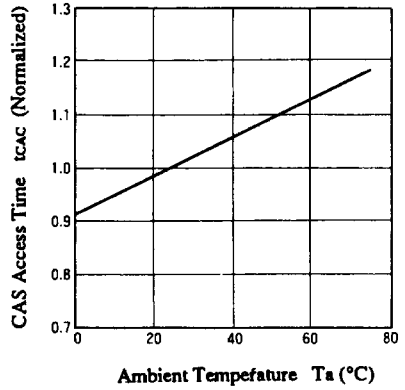
RAS Access Time vs. Ambient Temperature



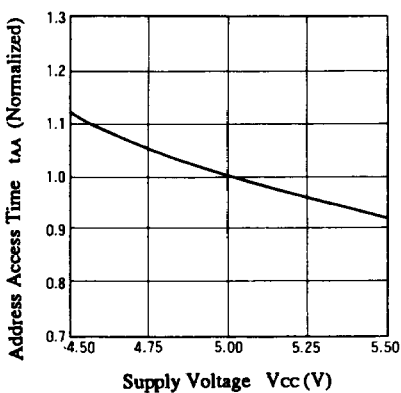
CAS Access Time vs. Supply Voltage



CAS Access Time vs. Ambient Temperature



Address Access Time vs. Supply Voltage



Address Access Time vs. Ambient Temperature

